

# PSMN3R0-60BS

# N-channel 60 V 3.2 mΩ standard level MOSFET in D2PAK Rev. 1 — 22 March 2012 Product data

**Product data sheet** 

#### 1. **Product profile**

#### 1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
$I_D$	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see Figure 1	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics						
03011	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>		-	4.32	5.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13		-	2.7	3.2	mΩ
Dynamic c	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 30 \text{ V};$		-	28	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	130	-	nC
	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	-	800	mJ

<sup>[1]</sup> Continuous current is limited by package



# 2. Pinning information

Table 2. Pinning information

		•		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	nected to drain	mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make connection to pin 2

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R0-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN3R0-60BS	PSMN3R0-60BS

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<u> </u>				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	<u>[1]</u>	-	83.4	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3		-	824	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	306	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	ain diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$		-	824	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 60 V; $R_{GS}$ = 50 Ω; unclamped		-	800	mJ

#### [1] Continuous current is limited by package

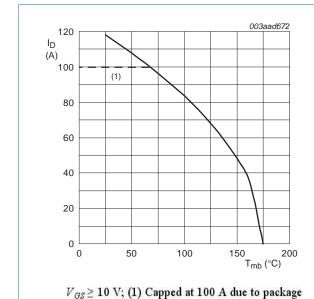


Fig 1. Continuous drain current as a function of mounting base temperature.

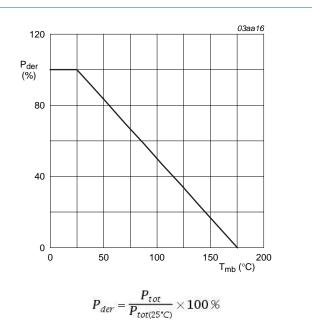


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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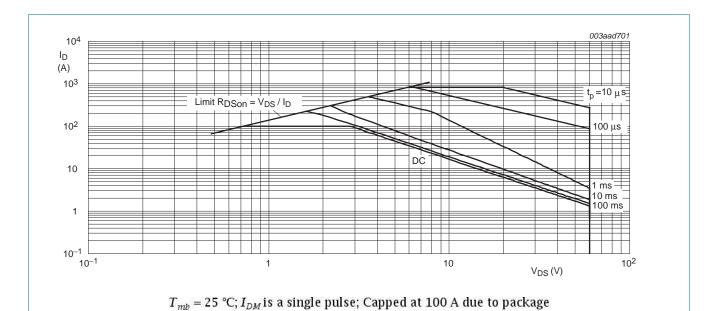


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted in a printed circuit board	-	50	-	K/W

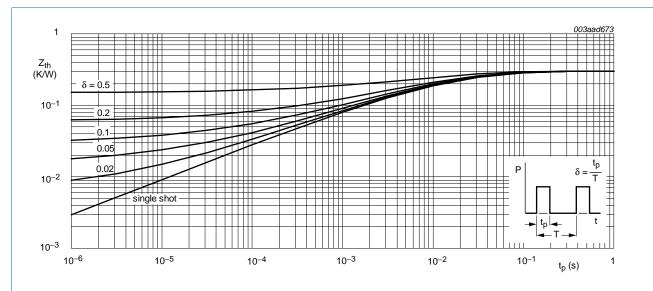


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V <sub>GSth</sub> gate-source threshold voltage	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 11</u>	1	-	-	V
	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	4.6	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R <sub>DSon</sub> drain-source on-st resistance	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.32	5.1	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see Figure 12; see Figure 13	-	6.21	7.3	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	2.7	3.2	mΩ	
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.1	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	110	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	130	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	43	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	21	-	nC
$Q_{GD}$	gate-drain charge		-	28	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 30 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.2	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{\text{Figure } 9}$	-	8079	-	pF
C <sub>oss</sub>	output capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{Figure 16}}$	-	971	-	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{\text{Figure } 16}; \text{ see } \frac{\text{Figure } 9}{\text{Figure } 16}$	-	492	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 10 \text{ V};$	-	31	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 1.5 \Omega$	-	26	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	77	-	ns
t <sub>f</sub>	fall time		-	22	-	ns

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.88	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;	-	54	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}$	-	97	-	nC

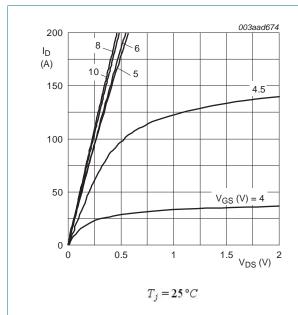


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

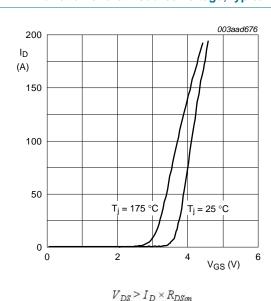
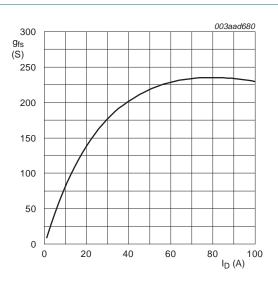
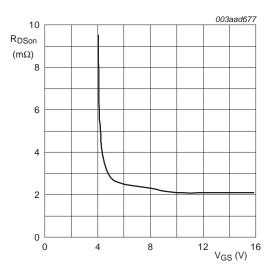


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25$  °C;  $V_{DS} = 30$ V

Fig 6. Forward transconductance as a function of drain current; typical values



 $T_j = 25$  °C;  $I_D = 25$  A

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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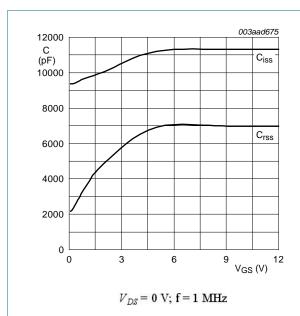


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

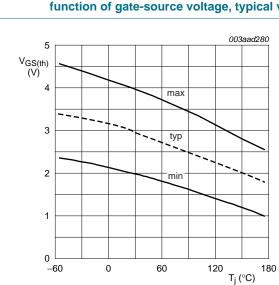
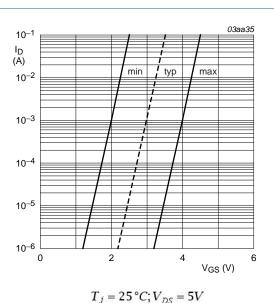


Fig 11. Gate-source threshold voltage as a function of junction temperature

 $I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$ 



 $T_j = 23$  C,  $V_{DS} = 3V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage

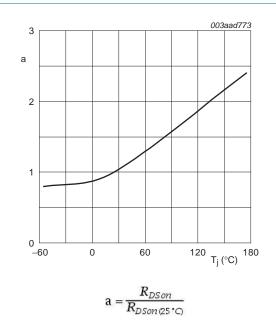
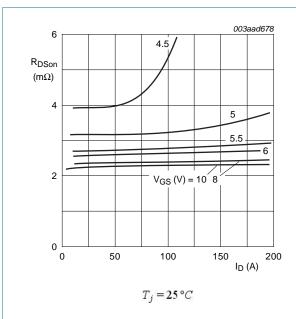


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



V<sub>DS</sub>

V<sub>GS(pl)</sub>

V<sub>GS(th)</sub>

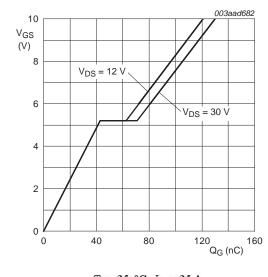
V<sub>GS</sub>

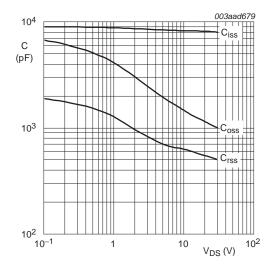
Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>G</sub>(tot)

003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions



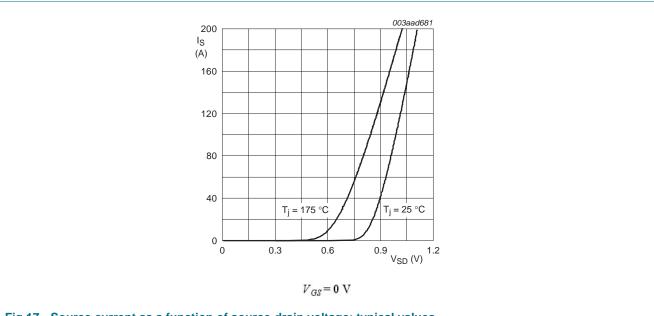


 $T_j = 25 \text{ °C}; I_D = 25 \text{ A}$ 

 $V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



# 8. Package outline

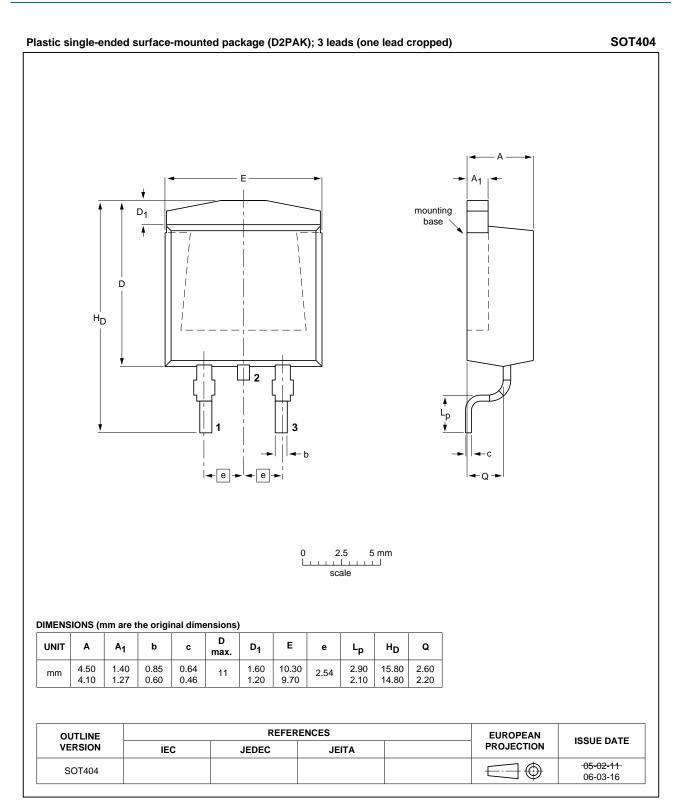


Fig 18. Package outline SOT404 (D2PAK)

# 9. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R0-60BS v.1	20120322	Product data sheet	-	-

## 10. Legal information

#### 10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# PSMN3R0-60BS

# **Nexperia**

#### N-channel 60 V 3.2 m $\Omega$ standard level MOSFET in D2PAK

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